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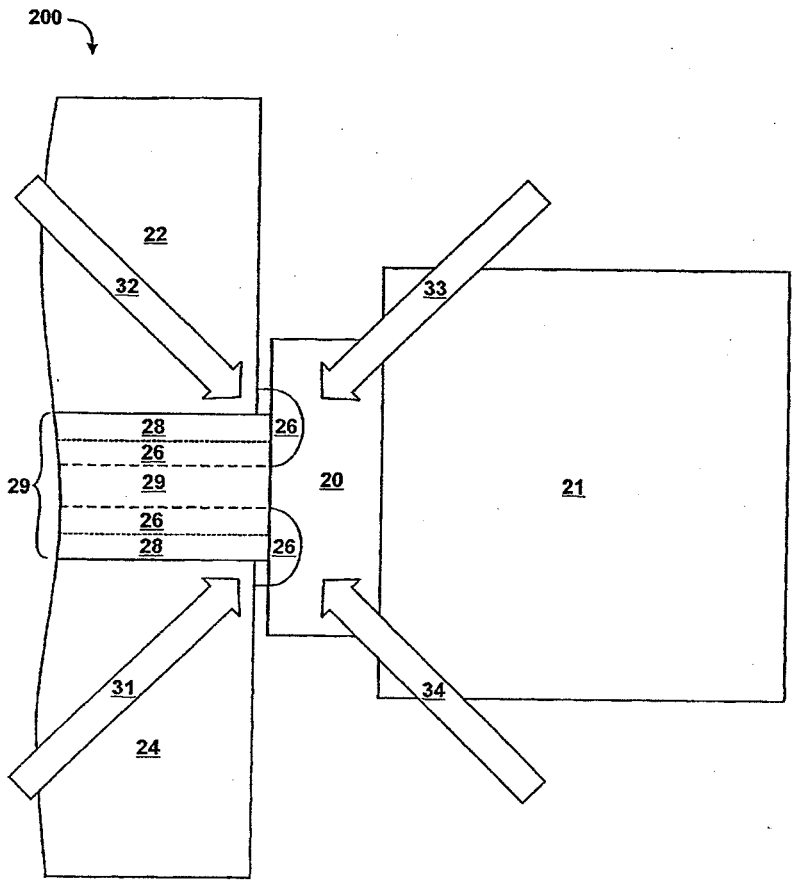
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(54) Title: BODY-TIED SOI TRANSISTOR AND METHOD FOR FABRICATION THEREOF




(57) Abstract: A method for fabricating a body-tied SOI transistor with reduced body resistance is presented. During the wafer fabrication process, a semiconductor wafer is placed in an ion implantation device and oriented to a first position relative to a beam path (31-34) of the ion implantation device in order to obtain a substantially non-orthogonal twist orientation between the beam path and the transistor gate (29) edge. Following this orientation of the first position, an ion species is implanted into a first implantation region. The wafer is then rotated to a second substantially non-orthogonal twist orientation, where another ion implantation is conducted. This process continues in the same manner, such that further substantially non-orthogonal twists and ion implantations are conducted, until the desired number of implantation areas is created. Halo or pocket implants are an example of the type of implantations to which the technique may be applied.

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